Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

Listing of Claims:

Claim 1 (currently amended): A ~~copper alloy~~ sputtering target, ~~wherein~~ comprising a copper alloy sputtering target containing 0.5 to 4.0wt% of Al and 0.5wtppm or less of Si ~~are contained~~, and having an average crystal grain size ~~is~~ of 0.1 to 60μm, and ~~the~~ an average grain size variation ~~is~~ of within ±20%.

Claim 2 (currently amended): A copper alloy sputtering target according to claim 1, wherein said target further ~~containing~~ contains one or more selected from among Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 1.0ppm or less.

Claim 3 (currently amended): A copper alloy sputtering target according to claim 1, wherein said target further ~~containing~~ contains one or more selected from among Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 0.5ppm or less.

Claim 4 (currently amended): A ~~copper alloy~~ sputtering target, ~~wherein~~ comprising a copper alloy sputtering target containing 0.5 to 4.0wt% of Sn and 0.5wtppm or less of Mn ~~are contained~~, and having an average crystal grain size ~~is~~ of 0.1 to 60μm, and ~~the~~ an average grain size variation ~~is~~ of within ±20%.

Claim 5 (currently amended): A copper alloy sputtering target according to claim 4, wherein said target further ~~containing~~ contains one or more selected from among Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 1.0ppm or less.

Claim 6 (currently amended): A copper alloy sputtering target according to claim 4, wherein said target further ~~containing~~ contains one or more selected from among Sb, Zr, Ti, Cr, Ag, Au, Cd, In and As in a total amount of 0.5ppm or less.

Claims 7-14 (canceled).

Claim 15 (new): A copper alloy sputtering target according to claim 3, wherein a recrystallization temperature of said target is 365°C or less.

Claim 16 (new): A copper alloy sputtering target according to claim 15, wherein said target contains 1wtppm or less of oxygen.

Claim 17 (new): A copper alloy sputtering target according to claim 16, wherein said target contains 0.5 to 4.0wt% of Sn.

Claim 18 (new): A copper alloy sputtering target according to claim 1, wherein a recrystallization temperature of said target is 365°C or less.

Claim 19 (new): A copper alloy sputtering target according to claim 1, wherein said target contains 5wtppm or less of oxygen.

Claim 20 (new): A copper alloy sputtering target according to claim 1, wherein said target contains 0.5 to 4.0wt% of Sn.

Claim 21 (new): A copper alloy sputtering target according to claim 6, wherein said target contains 1wtppm or less of oxygen.

Claim 22 (new): A copper alloy sputtering target according to claim 21, wherein said target contains 0.5 to 4.0wt% of Al.

Claim 23 (new): A copper alloy sputtering target according to claim 4, wherein a recrystallization temperature of said target is 365°C or less.

Claim 24 (new): A copper alloy sputtering target according to claim 4, wherein said target contains 5wtppm or less of oxygen.

Claim 25 (new): A copper alloy sputtering target according to claim 4, wherein said target contains 0.5 to 4.0wt% of Al.

Claim 26 (new): Semiconductor element wiring prepared by a process comprising the step of forming the semiconductor element wiring from a copper alloy sputtering target containing 0.5 to 4.0wt% of Al or Sn and 0.5wtppm or less of Si or Mn and having an average crystal grain size of 0.1 to 60μm and an average grain size variation of within ±20%.

Claim 27 (new): Semiconductor element wiring according to claim 26, wherein said semiconductor element wiring is a semiconductor wiring seed layer.

Claim 28 (new): Semiconductor element wiring according to claim 27, wherein said semiconductor wiring seed layer is formed on a barrier film of Ta, Ta alloy, or a nitride thereof.